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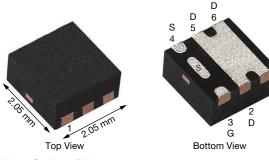
SiA437DJ



P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) (Max.)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)		
-20	0.0145 at V <sub>GS</sub> = -4.5 V	-29.7			
	0.0205 at V <sub>GS</sub> = -2.5 V	-25	28 nC		
	0.0330 at V <sub>GS</sub> = -1.8 V	-19.7	20110		
	0.0650 at V <sub>GS</sub> = -1.5 V	-4			

#### PowerPAK<sup>®</sup> SC-70-6L Single

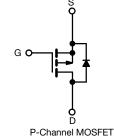


#### FEATURES

- TrenchFET<sup>®</sup> power MOSFET
- Thermally enhanced PowerPAK<sup>®</sup> SC-70 package **RoHS** Small footprint area
  - Low On-Resistance
- 100 % R<sub>a</sub> tested
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **APPLICATIONS**

- Providing low voltage drop in smart phones, tablet PCs, mobile computing:
- Battery switches
  - Load switches
- Power management



Marking Code: BU

Ordering Information:

SiA437DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	-20		
Gate-Source Voltage		V <sub>GS</sub>	± 8	- V	
	T <sub>C</sub> = 25 °C		-29.7		
	T <sub>C</sub> = 70 °C		-23.8		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>A</sub> = 25 °C	I <sub>D</sub>	-12.6 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C		-10 <sup>b, c</sup>	А	
Pulsed Drain Current (t = 300 μs)		I <sub>DM</sub>	-60		
Continuous Courses Drain Diada Current	T <sub>C</sub> = 25 °C		-16		
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	I <sub>S</sub>	-2.9 <sup>b, c</sup>		
	T <sub>C</sub> = 25 °C		19		
Maximum Power Dissipation	T <sub>C</sub> = 70 °C	Б	12	w	
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.5 <sup>b, c</sup>	vv	
	T <sub>A</sub> = 70 °C		2.2 <sup>b, c</sup>		
Operating Junction and Storage Temperature R	T <sub>J</sub> , T <sub>stg</sub>	-50 to 150	°C		
Soldering Recommendations (Peak Temperature) d, e			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 5 s	R <sub>thJA</sub>	28	36	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	5.3	6.5	0/10	

Notes

a.  $T_C = 25 \text{ °C.}$ b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: Manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 80 °C/W.

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### 1



HALOGEN

FREE

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	<u> </u>				<u> </u>	1	
Drain-Source Breakdown Voltage	$V_{DS}$ $V_{GS} = 0 V, I_D = -250 \mu A$		-20	-	-	V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$			-11	-		
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = -250 μA	-	2.5	-	mV/°C	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -250 \ \mu A$	-0.4	-	-0.9	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 8 V$		-	± 100	nA	
		V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V		-1			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ = -20 V, $V_{GS}$ = 0 V, $T_{J}$ = 55 °C	-	-	-10	μA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-10	-	-	А	
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -8 A	-	0.0120	0.0145	- Ω	
		V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -5 A	-	0.0170	0.0205		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -1.8 V, I <sub>D</sub> = -2 A	-	0.0250	0.0330		
		V <sub>GS</sub> = -1.5 V, I <sub>D</sub> = -2 A	-	0.0370	0.0650		
Forward Transconductance a	g <sub>fs</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -8 A	-	32	-	S	
Dynamic <sup>b</sup>						<u> </u>	
Input Capacitance	C <sub>iss</sub>		-	2340	-	pF	
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	305	-		
Reverse Transfer Capacitance	C <sub>rss</sub>		-	270	-		
	Qg	$V_{DS} = -10 \text{ V}, \text{ V}_{GS} = -8 \text{ V}, \text{ I}_{D} = -13 \text{ A}$	-	60	90	-	
Total Gate Charge			-	28	43	nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -10 \text{ V}, \text{ V}_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -13 \text{ A}$	-	4.2	-		
Gate-Drain Charge	Q <sub>gd</sub>		-	6.8	-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz	1.6	8	16	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>		-	20	40	- ns	
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, \text{ R}_{\text{I}} = 1 \Omega$	-	22	45		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong -10 \text{ A}, \text{ V}_{\text{GEN}} = -4.5 \text{ V}, \text{ R}_g = 1 \Omega$	-	100	200		
Fall Time	t <sub>f</sub>		-	37	75		
Turn-On Delay Time	t <sub>d(on)</sub>		-	10	20		
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, \text{ R}_{\text{I}} = 1 \Omega$		10	20	1	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong -10 \text{ A}, V_{GEN} = -8 \text{ V}, R_g = 1 \Omega$	-	120	240	-	
Fall Time	t <sub>f</sub>		-	34	70		
Drain-Source Body Diode Characterist	11			1	I		
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	-16	A	
Pulse Diode Forward Current	I <sub>SM</sub>		-	-	-60		
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = -10 A, V <sub>GS</sub> = 0 V	-	-0.75	-1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>			12	25	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	1	-	4	10	nC	
		$I_F$ = -10 A, dI/dt = 100 A/µs, $T_J$ = 25 °C	_				
Reverse Recovery Fall Time	t <sub>a</sub>		-	7.5	-		

#### Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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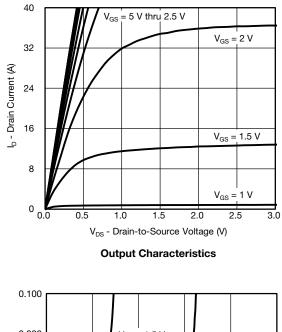
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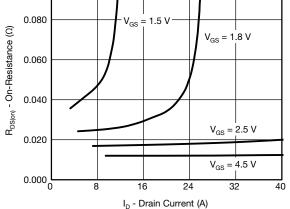


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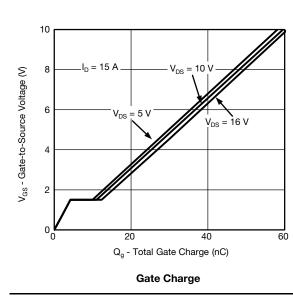
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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



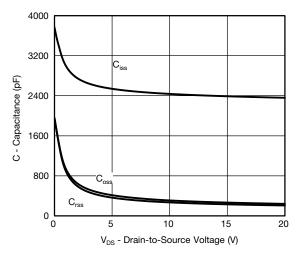


**On-Resistance vs. Drain Current and Gate Voltage** 

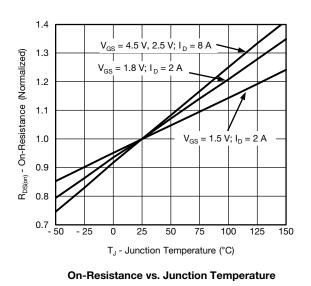


10 8 I<sub>D</sub> - Drain Current (A) T<sub>C</sub> = 25 6 4 T<sub>C</sub> = 125 °C 2 55 °C Тc 0.0 0.4 0.8 1.2 1.6 2.0 V<sub>GS</sub> - Gate-to-Source Voltage (V)

Transfer Characteristics







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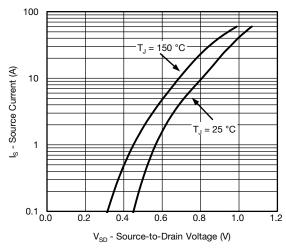
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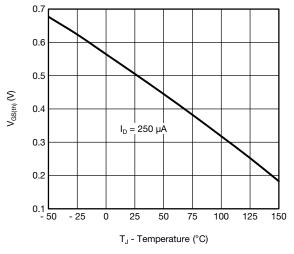


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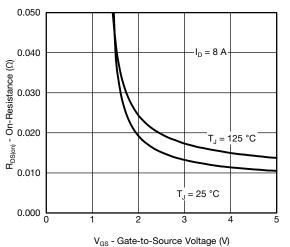
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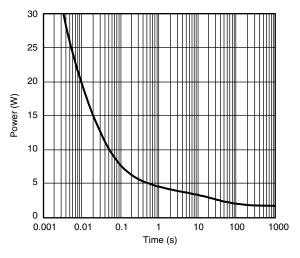
Source-Drain Diode Forward Voltage



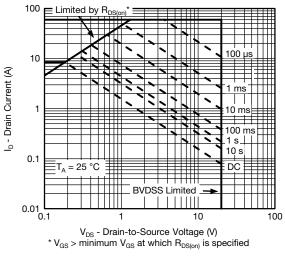
**Threshold Voltage** 



**On-Resistance vs. Gate-to-Source Voltage** 



Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient 4

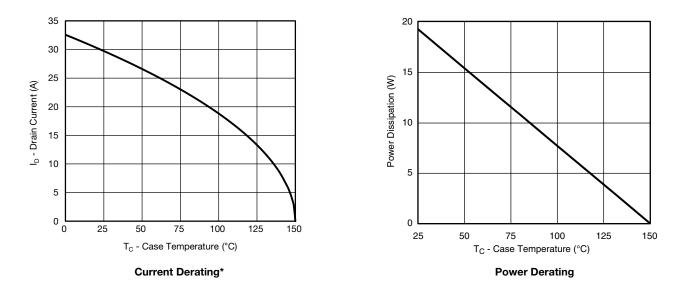
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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

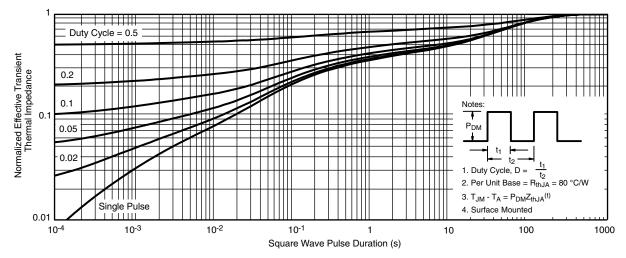


\* The power dissipation PD is based on TJ (max.) = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

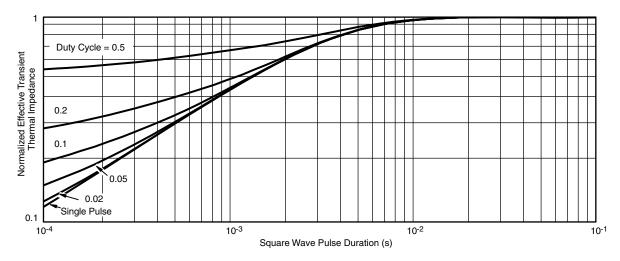


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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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## PowerPAK<sup>®</sup> SC70-6L

VISHA

# b PIN2 PIN1 PIN3 \_ ₹



b

PIN3

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PIN2

PIN1

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### RECOMMENDED PAD LAYOUT FOR PowerPAK<sup>®</sup> SC70-6L Single



Dimensions in mm/(Inches)

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Revision: 01-Jan-2025

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